Ordering number : ENN6780

N-Channel Silicon MOSFET

MCH6403

Ultrahigh-Speed Switching Applications

Features

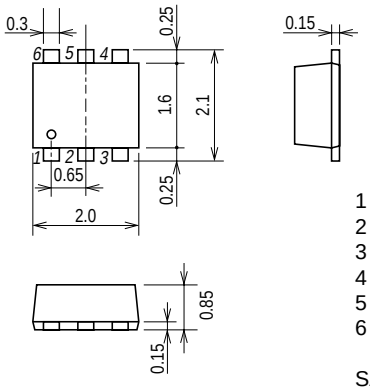
- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

Package Dimensions

unit : mm

2193

[MCH6403]



1 : Drain
2 : Drain
3 : Gate
4 : Source
5 : Drain
6 : Drain

SANYO : MCPH6

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		20	V
Gate-to-Source Voltage	V_{GSS}		±10	V
Drain Current (DC)	I_D		3	A
Drain Current (Pulse)	I_{DP}	PW≤10μs, duty cycle≤1%	12	A
Allowable Power Dissipation	P_D	Mounted on a ceramic board (900mm²×0.8mm)	1.4	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0	20			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=20V, V_{GS}=0			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±8V, V_{DS}=0			±10	μA
Cutoff Voltage	V_{GS}(off)	V_{DS}=10V, I_D=1mA	0.4		1.3	V
Forward Transfer Admittance	|yfs|	V_{DS}=10V, I_D=1.5A	3.3	4.8		S
Static Drain-to-Source On-State Resistance	R_{DS}(on)1	I_D=1.5A, V_{GS}=4V		80	105	mΩ
	R_{DS}(on)2	I_D=0.7A, V_{GS}=2.5V		110	155	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		200		pF
Output Capacitance	Coss	V_{DS}=10V, f=1MHz		70		pF
Reverse Transfer Capacitance	Crss	V_{DS}=10V, f=1MHz		45		pF

Marking : KC

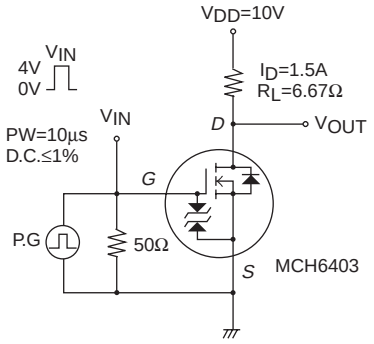
Continued on next page.

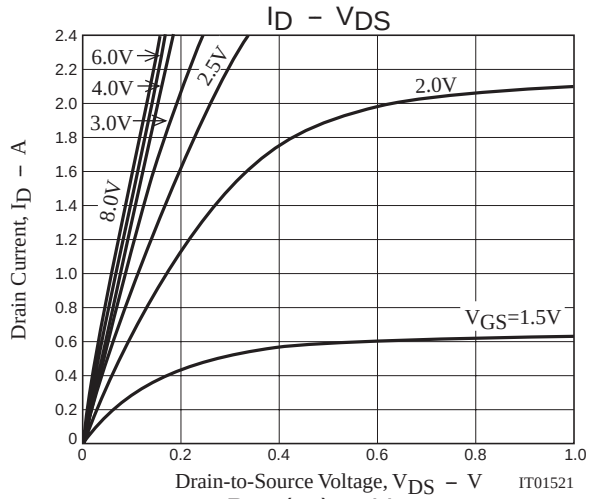
SANYO Electric Co.,Ltd. Semiconductor Company
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

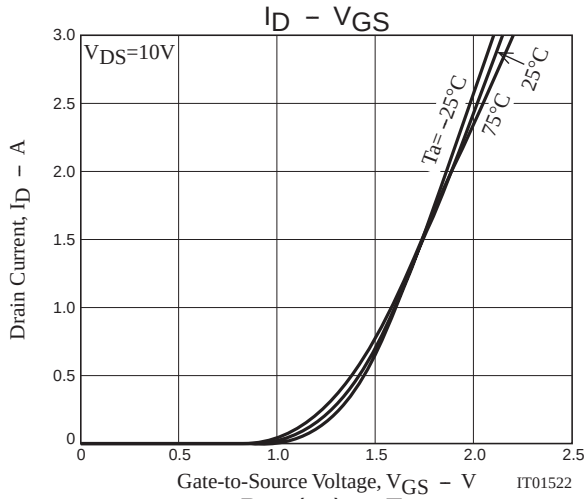
Continued from preceding page.

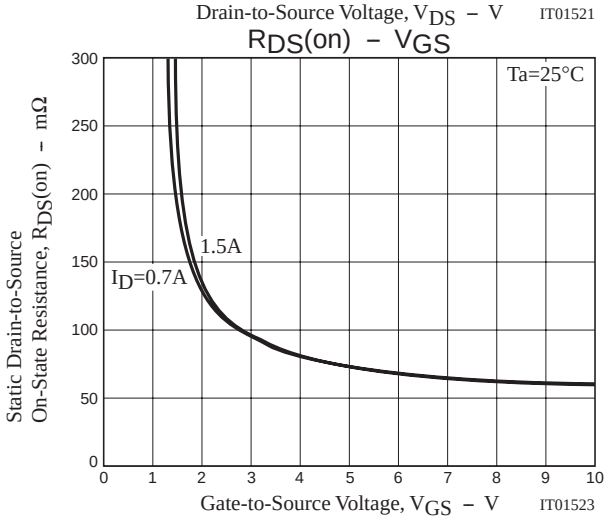
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Turn-ON Delay Time	t_{d}(on)	See specified Test Circuit		8		ns
Rise Time	t_r	See specified Test Circuit		45		ns
Turn-OFF Delay Time	t_{d}(off)	See specified Test Circuit		27		ns
Fall Time	t_f	See specified Test Circuit		45		ns
Total Gate Charge	Qg	V_{DS}=10V, V_{GS}=10V, I_D=3A		7		nC
Gate-to-Source Charge	Qgs	V_{DS}=10V, V_{GS}=10V, I_D=3A		0.5		nC
Gate-to-Drain “Miller” Charge	Qgd	V_{DS}=10V, V_{GS}=10V, I_D=3A		1		nC
Diode Forward Voltage	V_{SD}	I_S=3A, V_{GS}=0		0.87	1.2	V

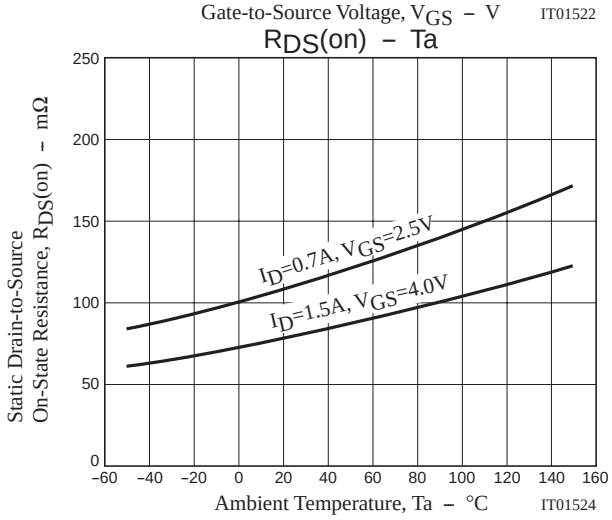
Switching Time Test Circuit

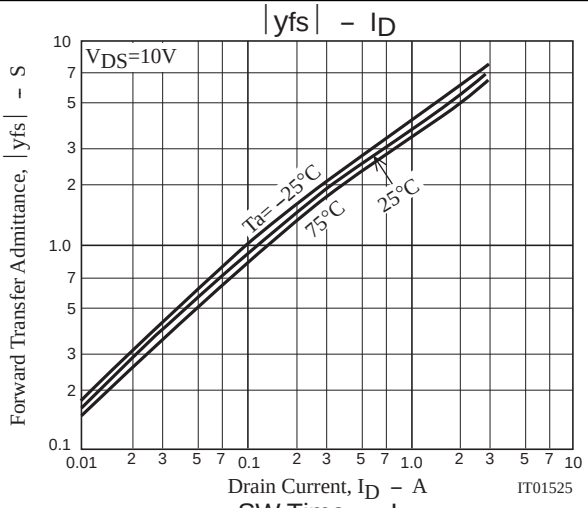


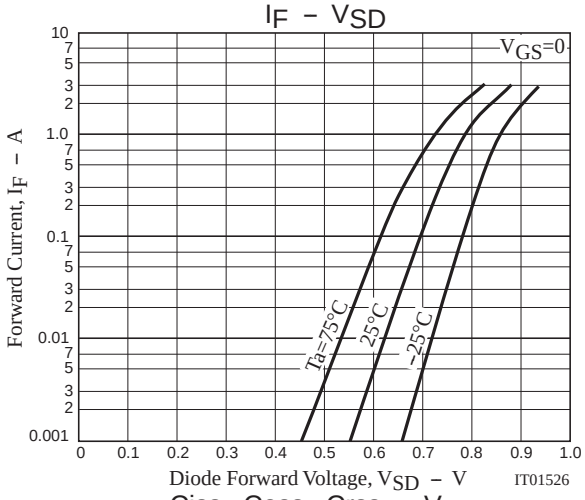


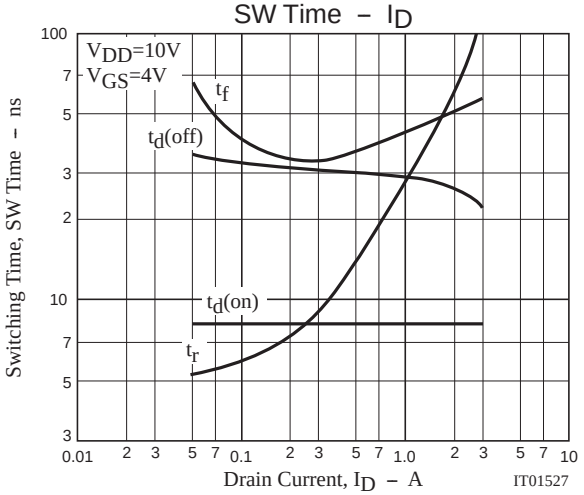


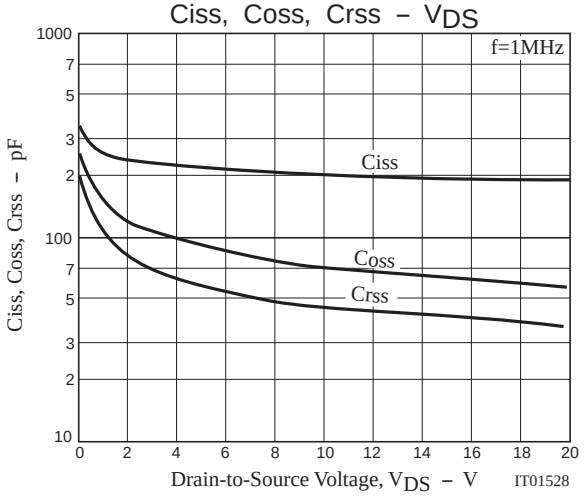


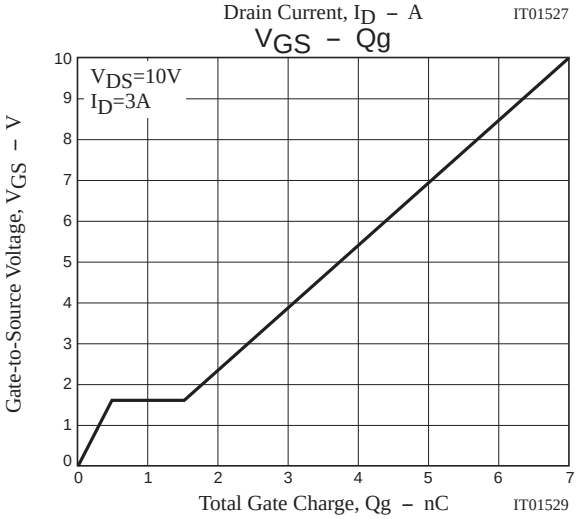


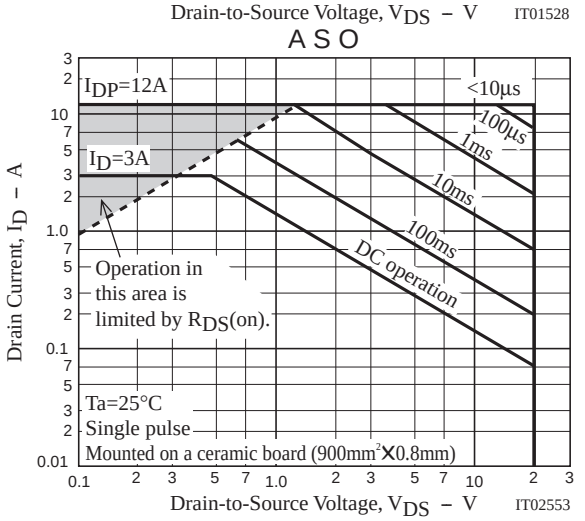

|yfs| – ID
VDS=10V
Ta=–25°C
75°C
25°C
Forward Transfer Admittance, |yfs| – S
Drain Current, ID – A
IT01525

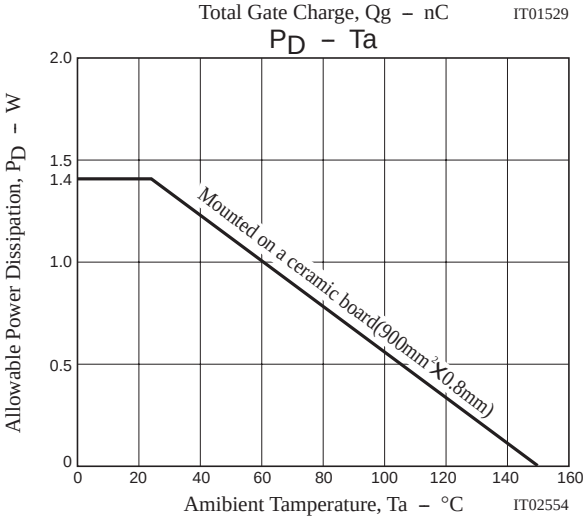

IF – VSD
VGS=0
Ta=75°C
25°C
–25°C
Forward Current, IF – A
Diode Forward Voltage, VSD – V
IT01526


SW Time – ID
VDD=10V
VGS=4V
tf
td(off)
td(on)
tr
Switching Time, SW Time – ns
Drain Current, ID – A
IT01527


Ciss, Coss, Crss – VDS
f=1MHz
Ciss
Coss
Crss
Ciss, Coss, Crss – pF
Drain-to-Source Voltage, VDS – V
IT01528


VGS – Qg
VDS=10V
ID=3A
Gate-to-Source Voltage, VGS – V
Total Gate Charge, Qg – nC
IT01529


A S O
IDP=12A
ID=3A
<10µs
100µs
1ms
10ms
100ms
DC operation
Operation in
this area is
limited by RDS(on).
Ta=25°C
Single pulse
Mounted on a ceramic board (900mm²×0.8mm)
Drain Current, ID – A
Drain-to-Source Voltage, VDS – V
IT02553


PD – Ta
Mounted on a ceramic board(900mm²×0.8mm)
Allowable Power Dissipation, PD – W
Amibient Tamperature, Ta – °C
IT02554